

Supplementary Materials

Opto-electrical evaluation of visible blind fast-response nanostructured SnO₂/Si photodetector

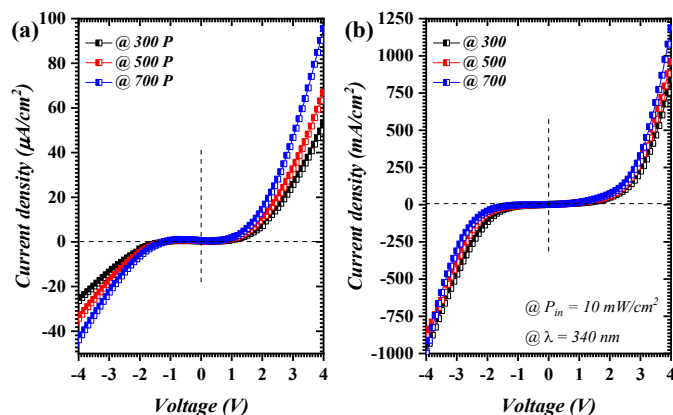


Figure S1: Opto-electrical features of the proposed devices as by means of laser pulses: (a) dark I-V and (b) illuminated I-V @ 340 nm, and 10 mW/cm².

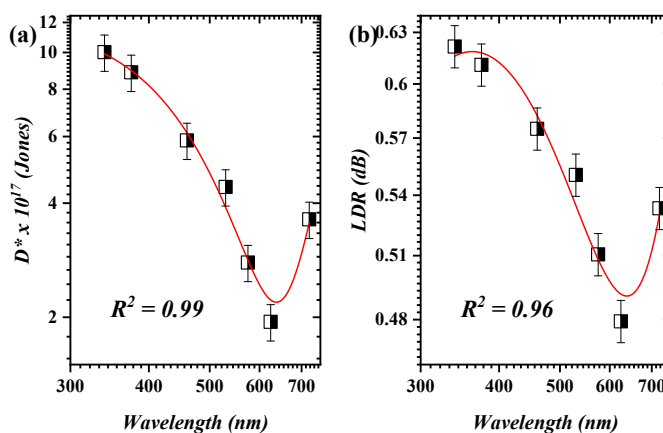


Figure S2: Opto-electrical features of the fabricated photodetector @ 700 pulses as a function of wavelength; (a) photo-detectivity and (b) linear dynamic range characteristics were attained @ 3 V and 10 mW/cm².

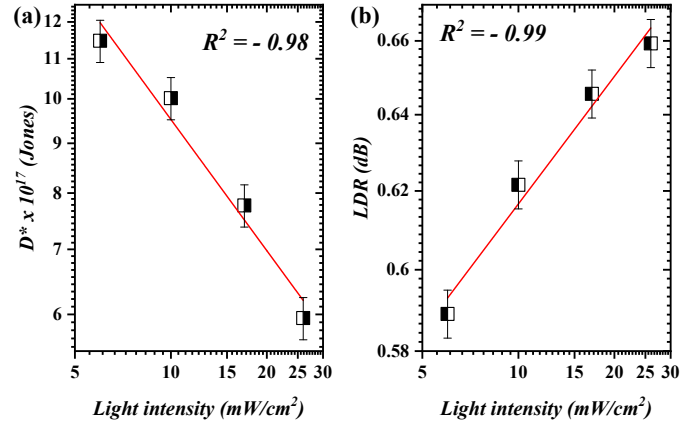


Figure S3: Opto-electrical features of the fabricated photodetector @ 700 pulses as a function of illumination power; (a) photo-detectivity and (b) linear dynamic range characteristics were attained @ 3 V and $\lambda = 340 \text{ nm}$.

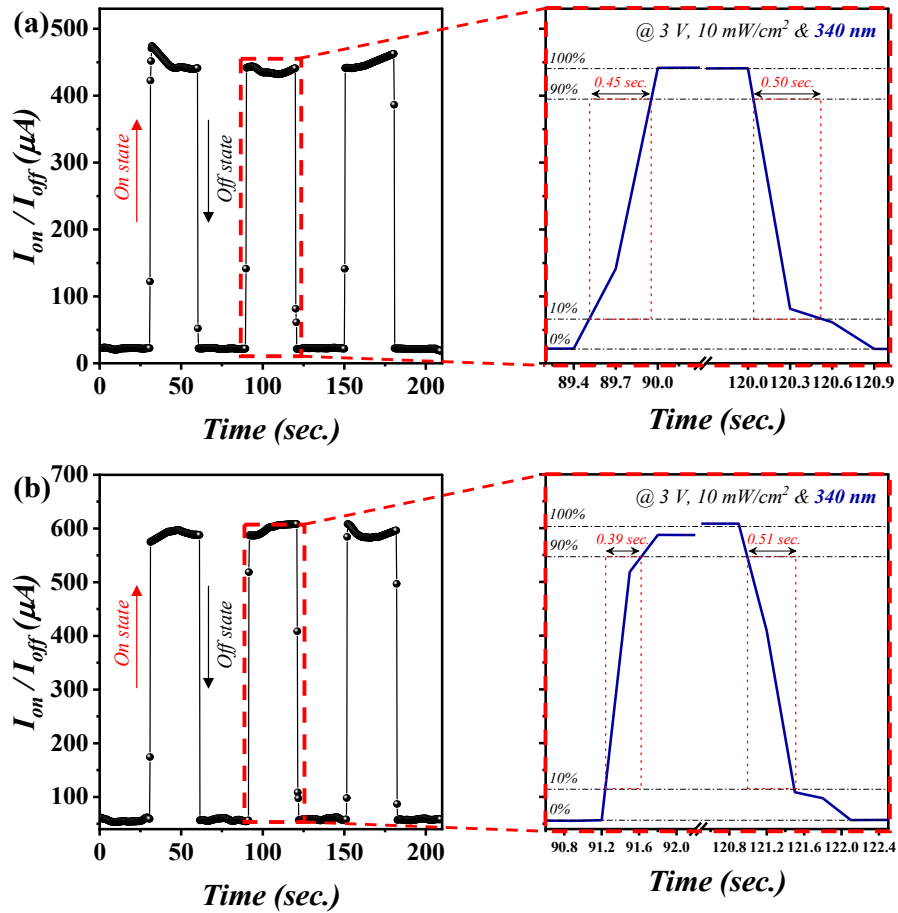


Figure S4: Time-resolved characteristics of the fabricated devices at (a) 300 pulses and (b) 500 pulses.